

Description

The PDCSD15CW is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers and PDA's, using monolithic silicon technology to provide fast response time and ultra low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The PDCSD15CW complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. The PDCSD15CW is assembled into a lead-free SOD-323 package and will protect one bidirectional line. These devices will fit on the same PCB pad area as an 0805 MLV device.

Features

- 250W peak pulse power (8/20µs)
- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage: 15V
- Ultra low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test Air discharge: ±30kV

Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 10A (8/20µs)
- RoHS Compliant

Mechanical Characteristics

Package: SOD-323Lead Finish: Matte Tin

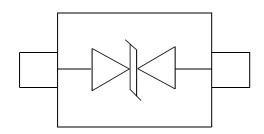
Case Material: "Green" Molding Compound.
Moisture Sensitivity: Level 3 per J-STD-020
Terminal Connections: See Diagram Below

• Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Peripherals
- Pagers Peripherals
- Desktop and Servers

Dimensions and Pin Configuration



Circuit and Pin Schematic

Marking Information

2J

2J =Device Marking Code

Ordering Information

Part Number	Marking	Packaging	Reel Size
PDCSD15CW	2J	3000/Tape & Reel	7 inch

www.pdwsemi.com



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

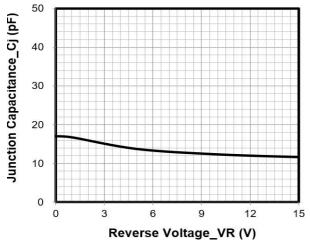
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	250	W
Peak Pulse Current (8/20µs)	lpp	10	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	±30 ±30	kV
Operating Temperature Range	TJ	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (TA=25°C unless otherwise specified)

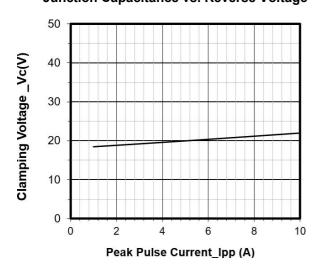
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			15	V	
Breakdown Voltage	VBR	16.5			V	IT = 1mA
Reverse Leakage Current	I _R			0.5	μA	VRWM = 15V
Clamping Voltage	Vc			20	V	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	Vc			25	V	IPP = 10A (8 x 20µs pulse)
Junction Capacitance	Cı		17		pF	VR = 0V, f = 1MHz



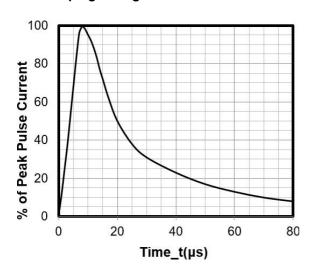
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



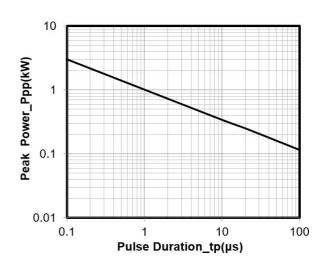
Junction Capacitance vs. Reverse Voltage



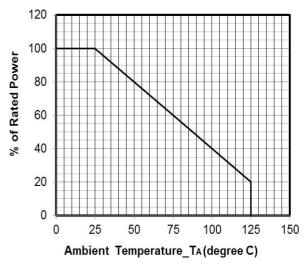
Clamping Voltage vs. Peak Pulse Current



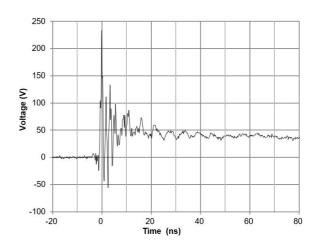
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



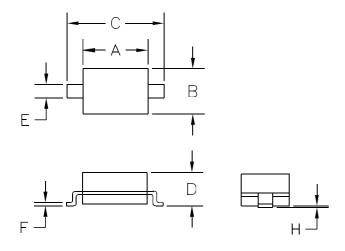
Power Derating Curve



ESD Clamping Voltage 8 kV Contact per IEC61000-4-2

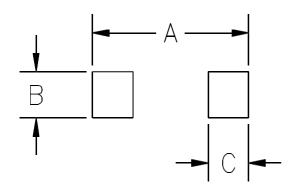


SOD-323 Package Outline Drawing



	DIMENSIO				
SYM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	1.50	1.80	0.060	0.071	
В	1.20	1.40	0.045	0.054	
С	2.30	2.70	0.090	0.107	
D	1	1.10	-	0.043	
Е	0.30	0.40	0.012	0.016	
F	0.10	0.25	0.004	0.010	
Н	1	0.10	-	0.004	

Suggested Land Pattern



CVM	DIMENSIONS				
SYM	MILLIMETERS	INCHES			
Α	3.15	0.120			
В	0.80	0.031			
С	0.80	0.031			